## HEWLETT-PACKARD COMPA

Intellectual Property Administ

P. O. Box 272400 Fort Collins, Colorado 80527-2400



## PATENT APPLICATION

ATTORNEY DOCKET NO. 10004808-1

### UNITED STATE ATENT AND TRADEMARK OFFICE

Inventor(s):

Osamu NAKAGAWA et al.

Confirmation No.: 3635

Applicati n N .:09/891,324

Examiner: L. SCHILLINGER

**Filing Date:** 

June 27, 2001

Group Art Unit: 2813

Title:

Sir:

PROCESS FOR HIGH-DIELECTRIC CONSTANT METAL-INSULATOR METAL CAPACITOR

IN VLSI MULTI-LEVEL METALLIZATION SYSTEMS

**COMMISSIONER FOR PATENTS** Washington, D.C. 20231

JAN 0 9 2003

# TRANSMITTAL LETTER FOR RESPONSE AND MENT 3600

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(1) FOR	(2) CLAIMS REMAINING AFTER AMENDMENT		(3) NUMBER EXTRA		(4) HIGHEST NUMBER PREVIOUSLY PAID FOR		(5) PRESENT EXTRA		(6) RATE		ADDITION FEES	
TOTAL CLAIMS	13		MINUS		20		=	0	х	\$18	\$	
INDEP. CLAIMS	1		MINUS		3		=	0	х	\$84	\$	
[ ] FIRS	ST PE	RESENTATION OF	A MULT	ΓIPLE	DEPENDENT	CLAIM			+	\$280	\$	
EXTENSION FEE	1	1ST MONTH \$110.00				MONTH 3RD MON 00.00 \$920.00		4TH MONTH \$1440.00			\$	•
								o	THER	FEES	\$	
					TOTAL AL	DITIONAL FI	EE FOR	THIS A	MEN	DMENT		

pursuant to 37 CFR 1.25. Additionally please charge any fees to Deposit Account 08-2025 under 37 CFR 1.16 through 1.21 inclusive, and any other sections in Title 37 of the Code of Federal Regulations that may regulate fees. A duplicate copy of this sheet is enclosed.

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231.

Date of Deposit:

Typed Name:

Signature:

Respectfully submitted,

Osamu NAKAGAWA et al.

Attorney/Agent for Applicant(s)

Reg. No. 33,771

Date: January 4, 2003

Telephone No.: (202) 663-6446

- Attach as First Page to Transmitted Papers -

Intellectual Property Administration P.O. Box 272400

Fort Collins, Colorado 80527-2400

Docket No. 10004808-1

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CAPACITOR IN VLSI MULTI-LEVEL METALLIZATION SYSTEMS

## RESPONSE UNDER 37 C.F.R. §1.111

**BOX NO-FEE AMENDMENT** 

Commissioner for Patents Washington, D.C. 20231

Sir:

RECEIVED

JAN 0 9 2003

GROUP 3600

In response to the Office Action mailed October 7, 2002, the Applicants respectfully t the Examiner to consider the following remarks:

REMARKS

REMARKS

Claims 14-19 have been withdrawn from consideration. Thus, claims 1-1% are request the Examiner to consider the following remarks:

pending.

## 35 U.S.C. § 102(b) REJECTION OF CLAIMS 1-4 and 7-13

In the Office Action, claims 1-4 and 7-13 were rejected under 35 U.S.C. § 102(b) as allegedly being anticipated by Lou U.S. Pat. No. 6,162,680 (Lou). The Applicants respectfully traverse the rejection.

Claims 1-4 and 7-13 recite, inter alia, a method of forming a bypass capacitor that includes forming a first electrode in a first metal layer.